

# IRF7495PbF

HEXFET® Power MOSFET

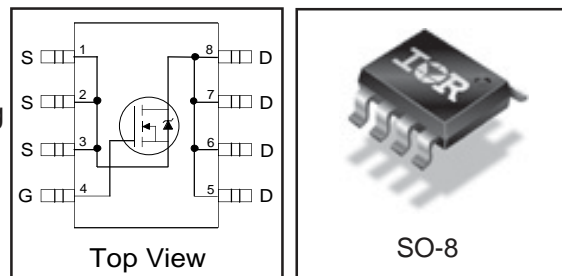
## Applications

- High frequency DC-DC converters
- Lead-Free

$V_{DSS}$	$R_{DS(on)}$ max	$I_D$
100V	22m $\Omega$ @ $V_{GS} = 10V$	7.3A

## Benefits

- Low Gate to Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective  $C_{OSS}$  to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



## Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	100	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	
$I_D$ @ $T_A = 25^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V	7.3	A
$I_D$ @ $T_A = 100^\circ C$	Continuous Drain Current, $V_{GS}$ @ 10V	4.6	
$I_{DM}$	Pulsed Drain Current ①	58	
$P_D$ @ $T_A = 25^\circ C$	Maximum Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/ $^\circ C$
dv/dt	Peak Diode Recovery dv/dt ②	7.3	V/ns
$T_J$	Operating Junction and	-55 to + 150	$^\circ C$
$T_{STG}$	Storage Temperature Range		

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	—	20	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ③	—	50	

Notes ① through ⑥ are on page 8  
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## Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.10	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	18	22	m $\Omega$	$V_{GS} = 10V, I_D = 4.4A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	$\mu A$	$V_{DS} = 100V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$

## Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

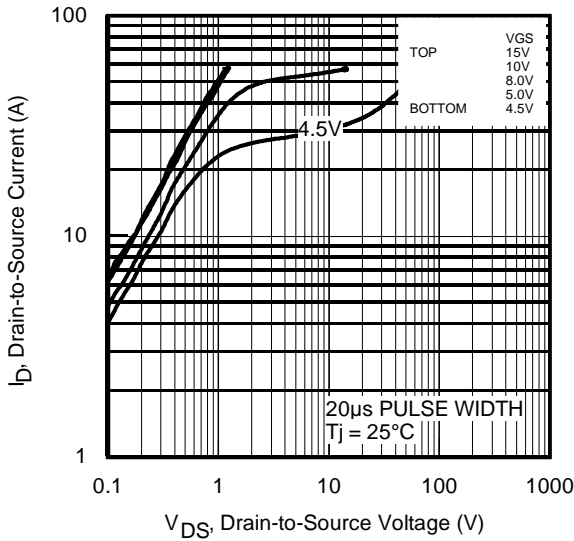
	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	11	—	—	S	$V_{DS} = 25V, I_D = 4.4A$
$Q_g$	Total Gate Charge	—	34	51	nC	$I_D = 4.4A$ $V_{DS} = 50V$ $V_{GS} = 10V$ ④
$Q_{gs}$	Gate-to-Source Charge	—	6.3	—		
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	11.7	—		
$t_{d(on)}$	Turn-On Delay Time	—	8.7	—	ns	$V_{DD} = 50V$ $I_D = 4.4A$ $R_G = 6.2\Omega$ $V_{GS} = 10V$ ④
$t_r$	Rise Time	—	13	—		
$t_{d(off)}$	Turn-Off Delay Time	—	10	—		
$t_f$	Fall Time	—	36	—		
$C_{iss}$	Input Capacitance	—	1530	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	250	—		$V_{DS} = 25V$
$C_{riss}$	Reverse Transfer Capacitance	—	110	—		$f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	980	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	160	—		$V_{GS} = 0V, V_{DS} = 80V, f = 1.0\text{MHz}$
$C_{oss\ eff.}$	Effective Output Capacitance	—	240	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 80V$ ⑤

## Avalanche Characteristics

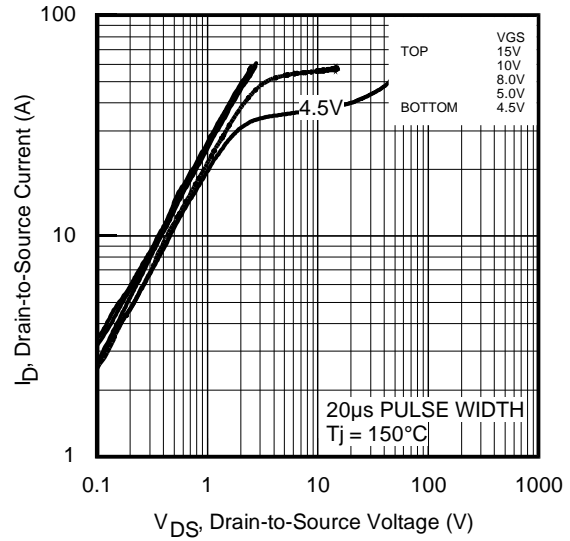
	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy ②	—	180	mJ
$I_{AR}$	Avalanche Current ①	—	4.4	A

## Diode Characteristics

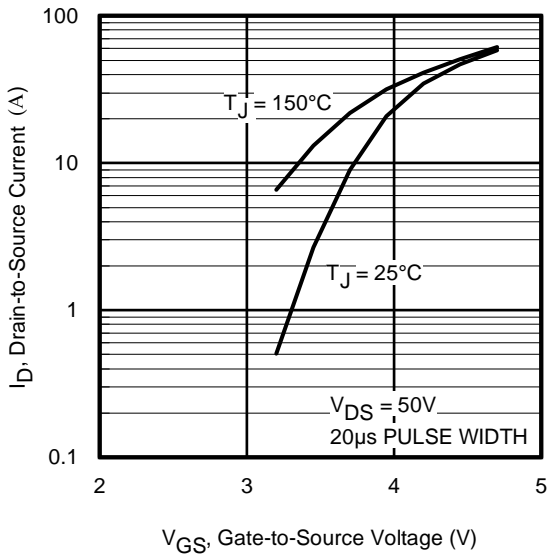
	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	2.3	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	58		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 4.4A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	42	—	ns	$T_J = 25^\circ\text{C}, I_F = 4.4A, V_{DD} = 25V$
$Q_{rr}$	Reverse Recovery Charge	—	73	—	nC	$di/dt = 100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				



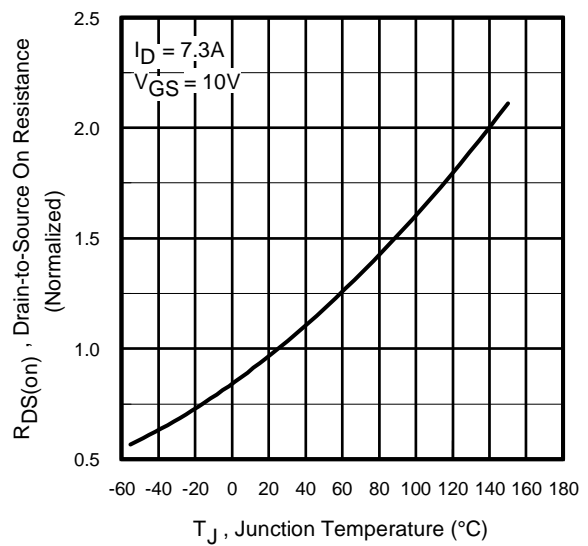
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

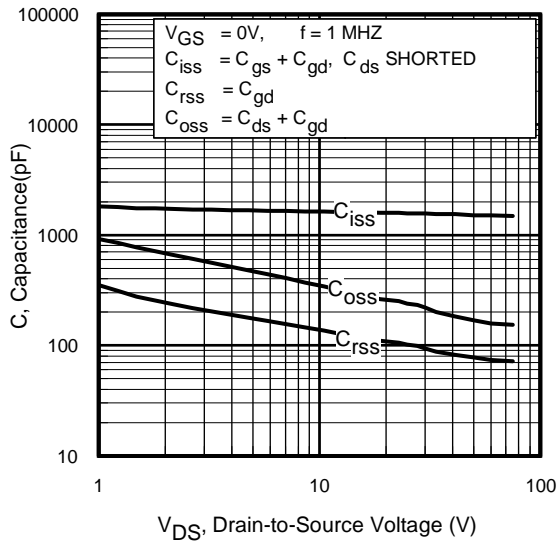


**Fig 3.** Typical Transfer Characteristics

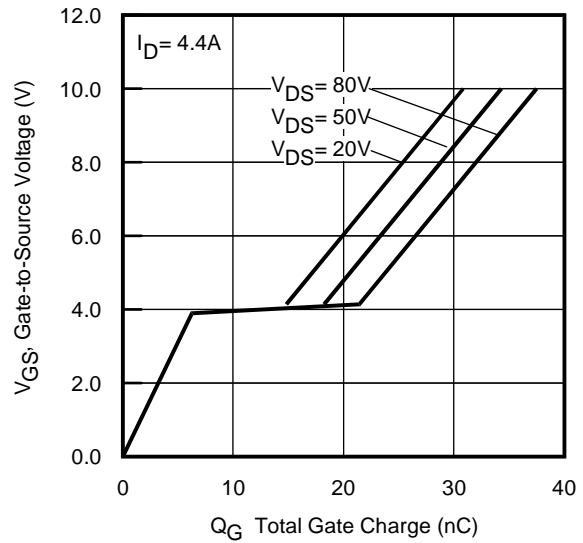


**Fig 4.** Normalized On-Resistance vs. Temperature

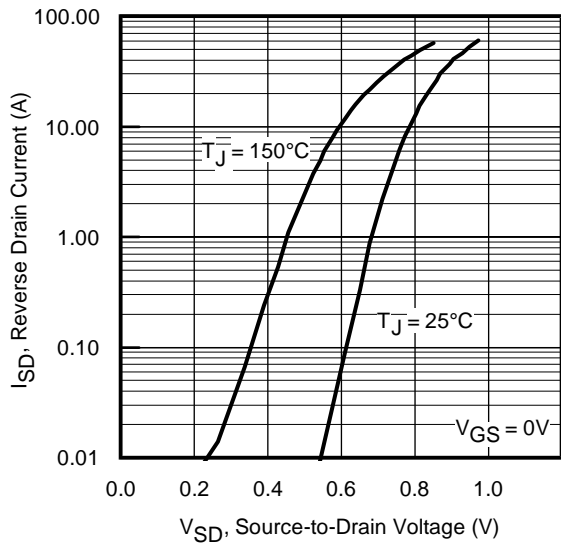
# IRF7495PbF



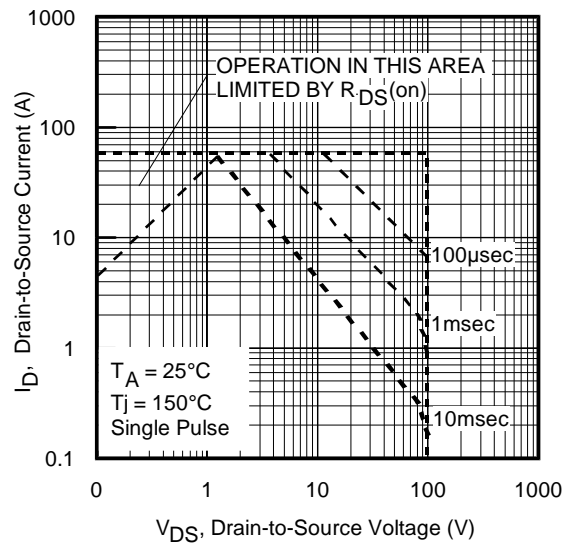
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



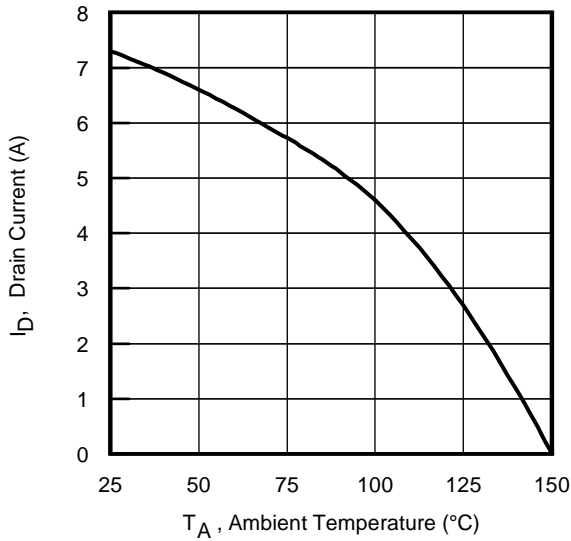
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



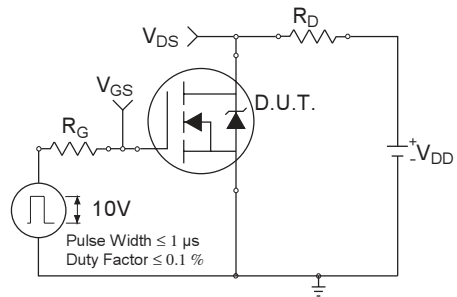
**Fig 7.** Typical Source-Drain Diode Forward Voltage



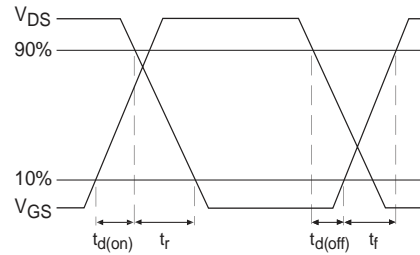
**Fig 8.** Maximum Safe Operating Area



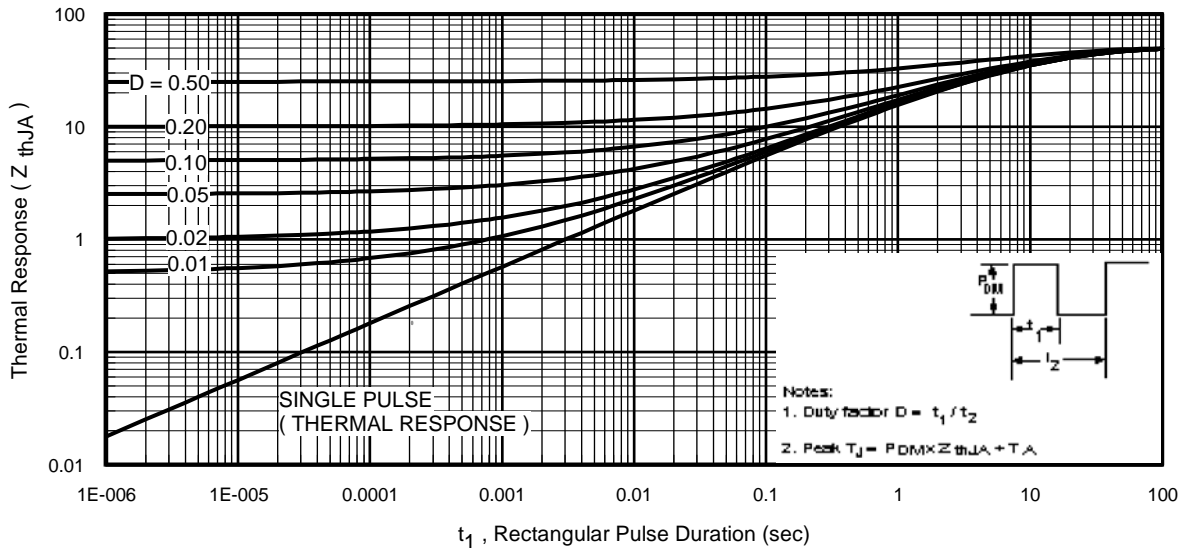
**Fig 9.** Maximum Drain Current vs. Ambient Temperature



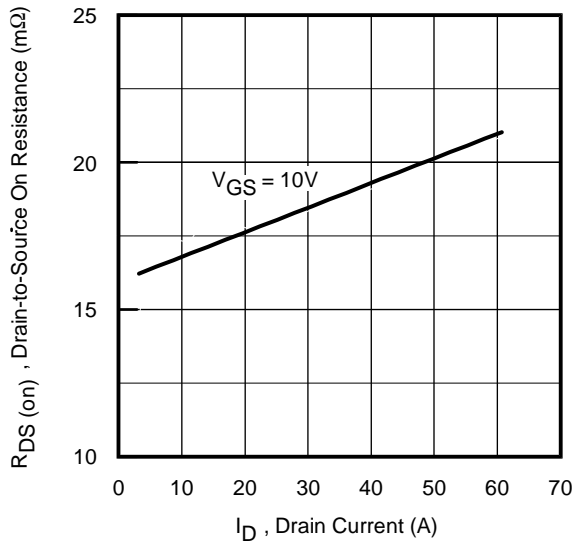
**Fig 10a.** Switching Time Test Circuit



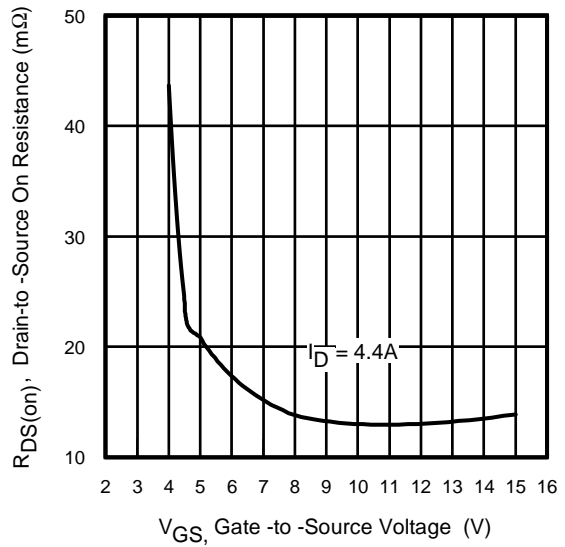
**Fig 10b.** Switching Time Waveforms



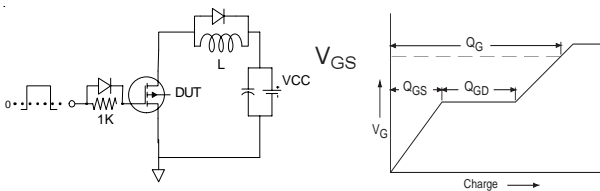
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



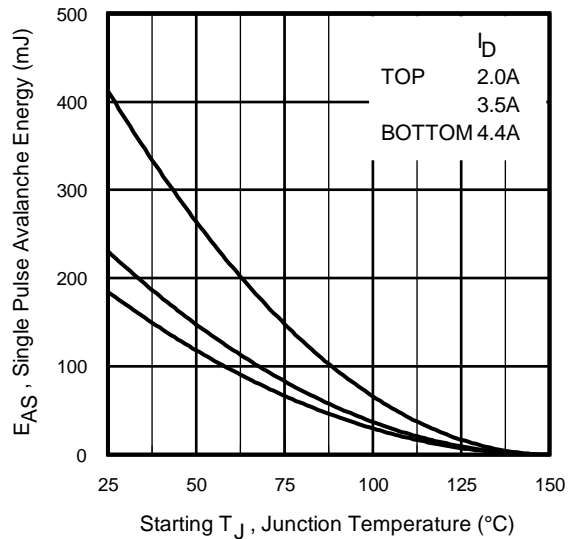
**Fig 12.** On-Resistance vs. Drain Current



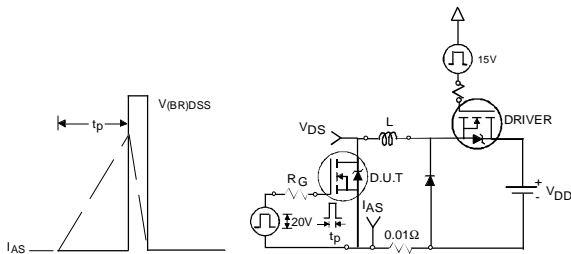
**Fig 13.** On-Resistance vs. Gate Voltage



**Fig 14a&b.** Basic Gate Charge Test Circuit and Waveform



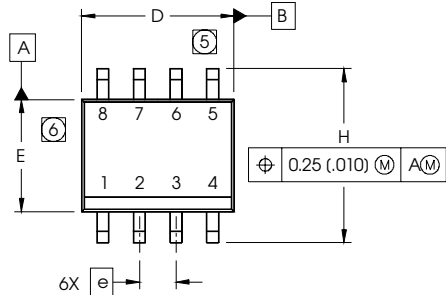
**Fig 15c.** Maximum Avalanche Energy vs. Drain Current



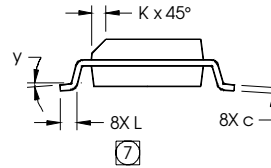
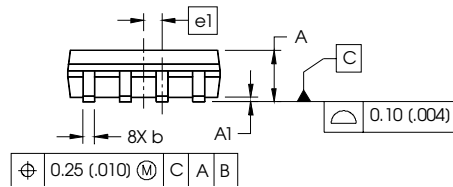
**Fig 15a&b.** Unclamped Inductive Test circuit and Waveforms

## SO-8 Package Outline

Dimensions are shown in millimeters (inches)



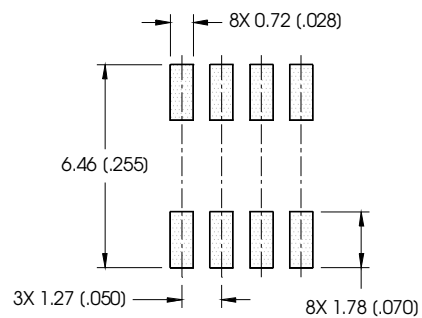
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



NOTES:

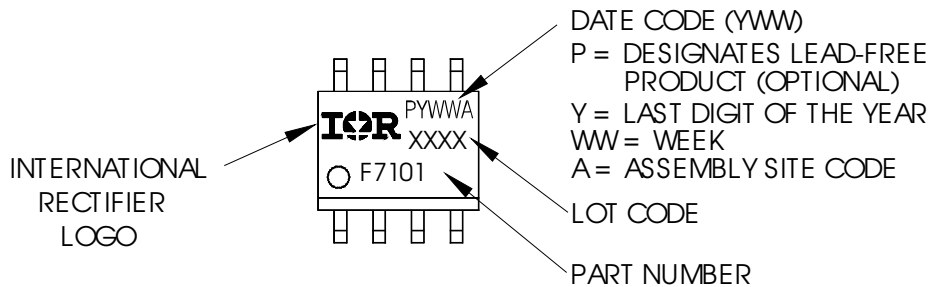
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- ⑤ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- ⑥ DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- ⑦ DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

FOOTPRINT



## SO-8 Part Marking

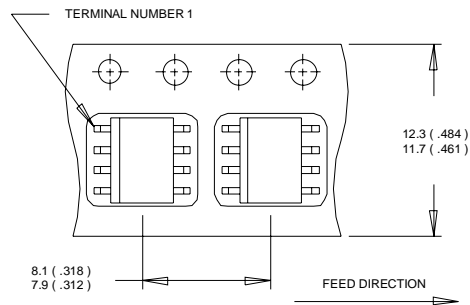
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



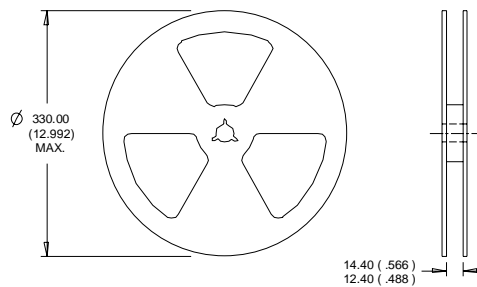
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## SO-8 Tape and Reel

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- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
  2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 19\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 4.4\text{A}$ .
- ③ When mounted on 1 inch square copper board,  $t \leq 10$  sec.
- ④ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{oss}$  eff. is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥  $I_{SD} \leq 5.8\text{A}$ ,  $di/dt \leq 250\text{A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 150^\circ\text{C}$ .

Data and specifications subject to change without notice.  
This product has been designed and qualified for the Consumer market.  
Qualifications Standards can be found on IR's Web site.

International  
**IR** Rectifier

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